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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	235
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p600l-fgg484i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Global Resources in Low Power Flash Devices

	,	,
Differential I/O Pairs	GAAO/IOuxwByVz	The output of the different pair will drive the global.
	GAA1/IOuxwByVz	
	GABO/IOuxwByVz	The output of the different pair will drive the global.
	GAB1/IOuxwByVz	
	GACO/IOuxwByVz	The output of the different pair will drive the global.
	GAC1/IOuxwByVz	
	GBAO/IOuxwByVz	The output of the different pair will drive the global.
	GBA1/IOuxwByVz	
	GBBO/IOuxwByVz	The output of the different pair will drive the global.
	GBB1/IOuxwByVz	
	GBCO/IOuxwByVz	The output of the different pair will drive the global.
	GBC1/IOuxwByVz	
	GDAO/IOuxwByVz	The output of the different pair will drive the global.
	GDA1/IOuxwByVz	
	GDBO/IOuxwByVz	The output of the different pair will drive the global.
	GDB1/IOuxwByVz	
	GDCO/IOuxwByVz	The output of the different pair will drive the global.
	GDC1/IOuxwByVz	
	GEAO/IOuxwByVz	The output of the different pair will drive the global.
	GEA1/IOuxwByVz	
	GEBO/IOuxwByVz	The output of the different pair will drive the global.
	GEB1/IOuxwByVz	
	GECO/IOuxwByVz	The output of the different pair will drive the global.
	GEC1/IOuxwByVz	

Table 3-3 • Quadrant Global Pin Name (continued)

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

Unused Global I/O Configuration

The unused clock inputs behave similarly to the unused Pro I/Os. The Microsemi Designer software automatically configures the unused global pins as inputs with pull-up resistors if they are not used as regular I/O.

I/O Banks and Global I/O Standards

In low power flash devices, any I/O or internal logic can be used to drive the global network. However, only the global macro placed at the global pins will use the hardwired connection between the I/O and global network. Global signal (signal driving a global macro) assignment to I/O banks is no different from regular I/O assignment to I/O banks with the exception that you are limited to the pin placement location available. Only global signals compatible with both the VCCI and VREF standards can be assigned to the same bank.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.





SmartGen also allows the user to select the various delays and phase shift values necessary to adjust the phases between the reference clock (CLKA) and the derived clocks (GLA, GLB, GLC, YB, and YC). SmartGen allows the user to select the input clock source. SmartGen automatically instantiates the special macro, PLLINT, when needed.



Note: Clock divider and clock multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.

Figure 4-6 • CCC with PLL Block

Global Input Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a CCC functional block or to a global / quadrant global network. Figure 4-7 on page 88 and Figure 4-8 on page 88 show the detailed architecture of each global input structure for 30 k gate devices and below, as well as 60 k gate devices and above, respectively. For 60 k gate devices and above (Figure 4-7 on page 88), if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen (not applicable for IGLOO nano and ProASIC3 nano devices), the first and second inputs are considered as paired, and the third input is paired with a regular I/O.

The user then has the choice of selecting one of the two sets to be used as the clock input source to the CCC functional block. There is also the option to allow an internal clock signal to feed the global network or the CCC functional block. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

CCC Locations

CCCs located in the middle of the east and west sides of the device access the three VersaNet global networks on each side (six total networks), while the four CCCs located in the four corners access three quadrant global networks (twelve total networks). See Figure 4-13.



Figure 4-13 • Global Network Architecture for 60 k Gate Devices and Above

The following explains the locations of the CCCs in IGLOO and ProASIC3 devices:

In Figure 4-15 on page 98 through Figure 4-16 on page 98, CCCs with integrated PLLs are indicated in red, and simplified CCCs are indicated in yellow. There is a letter associated with each location of the CCC, in clockwise order. The upper left corner CCC is named "A," the upper right is named "B," and so on. These names finish up at the middle left with letter "F."

ProASIC3L FPGA Fabric User's Guide

DYNCCC Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN), .GLA(GLA), .LOCK(LOCK), .CLKB(CLKB), .GLB(GLB), .YB(), .CLKC(CLKC), .GLC(GLC), .YC(), .SDIN(SDIN), .SCLK(SCLK), .SSHIFT(SSHIFT), .SUPDATE(SUPDATE), .MODE(MODE), .SDOUT(SDOUT), .OADIV0(GND), .OADIV1(GND), .OADIV2(VCC), .OADIV3(GND), .OADIV4(GND), .OAMUX0(GND), .OAMUX1(GND), .OAMUX2(VCC), .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND), .DLYGLA3(GND), .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND), .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND), .OBMUX2(GND), .DLYYB0(GND), .DLYYB1(GND), .DLYYB2(GND), .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND), .DLYGLB1(GND), .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND), .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND), .OCMUX0(GND), .OCMUX1(GND), .OCMUX2(GND), .DLYYC0(GND), .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND), .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND), .DLYGLC4(GND), .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(VCC), .FINDIV3(GND), .FINDIV4(GND), .FINDIV5(GND), .FINDIV6(GND), .FBDIV0(GND), .FBDIV1(GND), .FBDIV2(GND), .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(VCC), .FBDIV6(GND), .FBDLY0(GND), .FBDLY1(GND), .FBDLY2(GND), .FBDLY3(GND), .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND), .XDLYSEL(GND), .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(VCC)); defparam Core.VCOFREQUENCY = 165.000;

endmodule

Delayed Clock Configuration

The CLKDLY macro can be generated with the desired delay and input clock source (Hardwired I/O, External I/O, or Core Logic), as in Figure 4-28.

Figure 4-28 • Delayed Clock Configuration Dialog Box

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
Macro Parameters
*****
                               : delay_macro
Name
Family
                               : ProASIC3
                               : Verilog
Output Format
                               : Delayed Clock
Type
Delay Index
                               : 2
CLKA Source
                               : Hardwired I/O
Total Clock Delay = 0.935 ns.
The resultant CLKDLY macro Verilog netlist is as follows:
module delay_macro(GL,CLK);
output GL;
input CLK;
```

Figure 4-36 • Second-Stage PLL Showing Input of 256 MHz from First Stage and Final Output of 280 MHz

Figure 4-37 shows the simulation results, where the first PLL's output period is 3.9 ns (~256 MHz), and the stage 2 (final) output period is 3.56 ns (~280 MHz).

Stage 2 Output Clock Period Stage 1 Output Clock Period

Figure 4-37 • Model Sim Simulation Results

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Table 6-2 • Allowable Aspect Ratio Settings for WIDTHA[1:0]

WIDTHA[1:0]	WIDTHB[1:0]	D×W
00	00	4k×1
01	01	2k×2
10	10	1k×4
11	11	512×9

Note: The aspect ratio settings are constant and cannot be changed on the fly.

BLKA and BLKB

These signals are active-low and will enable the respective ports when asserted. When a BLKx signal is deasserted, that port's outputs hold the previous value.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, BLKB should be tied to ground.

WENA and WENB

These signals switch the RAM between read and write modes for the respective ports. A LOW on these signals indicates a write operation, and a HIGH indicates a read.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WENB should be tied to ground.

CLKA and CLKB

These are the clock signals for the synchronous read and write operations. These can be driven independently or with the same driver.

Note: For Automotive ProASIC3 devices, dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile.

PIPEA and PIPEB

These signals are used to specify pipelined read on the output. A LOW on PIPEA or PIPEB indicates a nonpipelined read, and the data appears on the corresponding output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the corresponding output in the next clock cycle.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, PIPEB should be tied to ground. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

WMODEA and WMODEB

These signals are used to configure the behavior of the output when the RAM is in write mode. A LOW on these signals makes the output retain data from the previous read. A HIGH indicates pass-through behavior, wherein the data being written will appear immediately on the output. This signal is overridden when the RAM is being read.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WMODEB should be tied to ground.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

ADDRA and ADDRB

These are used as read or write addresses, and they are 12 bits wide. When a depth of less than 4 k is specified, the unused high-order bits must be grounded (Table 6-3 on page 155).

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

• Designer software will automatically facilitate falling-edge clocks by bubble-pushing the inversion to previous stages.







Figure 6-7 • RAM Block with Embedded FIFO Controller

The FIFOs maintain a separate read and write address. Whenever the difference between the write address and the read address is greater than or equal to the almost-full value (AFVAL), the Almost-Full flag is asserted. Similarly, the Almost-Empty flag is asserted whenever the difference between the write address and read address is less than or equal to the almost-empty value (AEVAL).

Due to synchronization between the read and write clocks, the Empty flag will deassert after the second read clock edge from the point that the write enable asserts. However, since the Empty flag is synchronized to the read clock, it will assert after the read clock reads the last data in the FIFO. Also, since the Full flag is dependent on the actual hardware configuration, it will assert when the actual physical implementation of the FIFO is full.

For example, when a user configures a 128×18 FIFO, the actual physical implementation will be a 256×18 FIFO element. Since the actual implementation is 256×18, the Full flag will not trigger until the

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Date	Changes	Page
v1.1 (continued)	Table 6-1 • Flash-Based FPGAs and associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	150
	The text introducing Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to replace "A3P030 and AGL030" with "15 k and 30 k gate devices." Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to remove AGL400 and AGLE1500 and include IGLOO PLUS and ProASIC3L devices.	162



I/O Structures in IGLOO and ProASIC3 Devices

GTL+ (Gunning Transceiver Logic Plus)

This is an enhanced version of GTL that has defined slew rates and higher voltage levels. It requires a differential amplifier input buffer and an open-drain output buffer. Even though the output is open-drain, VCCI must be connected to either 2.5 V or 3.3 V. The reference voltage (VREF) is 1 V.

Differential Standards

These standards require two I/Os per signal (called a "signal pair"). Logic values are determined by the potential difference between the lines, not with respect to ground. This is why differential drivers and receivers have much better noise immunity than single-ended standards. The differential interface standards offer higher performance and lower power consumption than their single-ended counterparts. Two I/O pins are used for each data transfer channel. Both differential standards require resistor termination.



Figure 7-7 • Differential Topology

LVPECL (Low-Voltage Positive Emitter Coupled Logic)

LVPECL requires that one data bit be carried through two signal lines; therefore, two pins are needed per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 850 mV. When the power supply is +3.3 V, it is commonly referred to as Low-Voltage PECL (LVPECL). Refer to the device datasheet for the full implementation of the LVPECL transmitter and receiver.

LVDS (Low-Voltage Differential Signal)

LVDS is a moderate-speed differential signaling system, in which the transmitter generates two different voltages that are compared at the receiver. LVDS uses a differential driver connected to a terminated receiver through a constant-impedance transmission line. It requires that one data bit be carried through two signal lines; therefore, the user will need two pins per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 350 mV. VCCI is 2.5 V. Low power flash devices contain dedicated circuitry supporting a high-speed LVDS standard that has its own user specification. Refer to the device datasheet for the full implementation of the LVDS transmitter and receiver.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) refers to bus interface circuits based on LVDS technology. Multipoint LVDS (M-LVDS) specifications extend the LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The driver requires series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus, since the driver can be located anywhere on the bus. These configurations can be implemented using TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 7-8. The input and output buffer delays are available in the LVDS sections in the datasheet.

Temporary overshoots are allowed according to the overshoot and undershoot table in the datasheet.



Figure 7-9 • Solution 1

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 7-10. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.





I/O Structures in IGLOO and ProASIC3 Devices

Related Documents

Application Notes

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL_AC276_AN.pdf

User's Guides

Libero SoC User's Guide http://www.microsemi.com.soc/documents/libero_ug.pdf IGLOO, Fusion, and ProASIC3 Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf SmartGen Core Reference Guide http://www.microsemi.com/soc/documents/genguide_ug.pdf

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Change	Page
August 2012	Figure 7-1 • DDR Configured I/O Block Logical Representation and Figure 7-2 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 38215).	175, 181
	AGL015 and A3P015 were added to Table 7-2 • Supported I/O Standards. 1.2 V was added under single-ended I/O standards. LVCMOS 1.2 was added to Table 7-3 • VCCI Voltages and Compatible IGLOO and ProASIC3 Standards (SAR 38096).	177
	Figure 7-4 • Simplified I/O Buffer Circuitry and Table 7-7 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3EL and RT ProASIC3 devices (SAR 39666).	183, 188
	The following sentence is incorrect and was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 40191):	184
	other devices there is no clamp diode.	
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	208, 210
June 2011	Figure 7-1 • DDR Configured I/O Block Logical Representation and Figure 7-2 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).	175, 181
	Table 7-1 • Flash-Based FPGAs was revised to remove RT ProASIC3 and addMilitary ProASIC3/EL in its place (SAR 31824, 31825).	176
	The "Advanced I/Os—IGLOO, ProASIC3L, and ProASIC3" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	177



Security in Low Power Flash Devices

3. Choose the desired settings for the FlashROM configurations to be programmed (Figure 12-13). Click **Finish** to generate the STAPL programming file for the design.

Figure 12-13 • FlashROM Configuration Settings for Low Power Flash Devices

Generation of Security Header Programming File Only— Application 2

As mentioned in the "Application 2: Nontrusted Environment—Unsecured Location" section on page 309, the designer may employ FlashLock Pass Key protection or FlashLock Pass Key with AES encryption on the device before sending it to a nontrusted or unsecured location for device programming. To achieve this, the user needs to generate a programming file containing only the security settings desired (Security Header programming file).

Note: If AES encryption is configured, FlashLock Pass Key protection must also be configured.

The available security options are indicated in Table 12-4 and Table 12-5 on page 317.

Security Option	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	-	-	_
FlashLock only	1	1	\checkmark
AES and FlashLock	1	1	\checkmark

Table 12-4 • FlashLock Security Options for IGLOO and ProASIC3

Figure 12-19 • FlashLock Pass Key, Previously Programmed Devices

It is important to note that when the security settings need to be updated, the user also needs to select the **Security settings** check box in Step 1, as shown in Figure 12-10 on page 314 and Figure 12-11 on page 314, to modify the security settings. The user must consider the following:

- If only a new AES key is necessary, the user must re-enter the same Pass Key previously
 programmed into the device in Designer and then generate a programming file with the same
 Pass Key and a different AES key. This ensures the programming file can be used to access and
 program the device and the new AES key.
- If a new Pass Key is necessary, the user can generate a new programming file with a new Pass Key (with the same or a new AES key if desired). However, for programming, the user must first load the original programming file with the Pass Key that was previously used to unlock the device. Then the new programming file can be used to program the new security settings.

Advanced Options

As mentioned, there may be applications where more complicated security settings are required. The "Custom Security Levels" section in the *FlashPro User's Guide* describes different advanced options available to aid the user in obtaining the best available security settings.

14 – Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming

Introduction

The IGLOO[®] and ProASIC[®]3L families offer devices that can be powered by either 1.5 V or, in the case of V2 devices, a core supply voltage anywhere in the range of 1.2 V to 1.5 V, in 50 mV increments.

Since IGLOO and ProASIC3L devices are flash-based, they can be programmed and reprogrammed multiple times in-system using Microsemi FlashPro3. FlashPro3 uses the JTAG standard interface (IEEE 1149.1) and STAPL file (defined in JESD 71 to support programming of programmable devices using IEEE 1149.1) for in-system configuration/programming (IEEE 1532) of a device. Programming can also be executed by other methods, such as an embedded microcontroller that follows the same standards above.

All IGLOO and ProASIC3L devices must be programmed with the VCC core voltage at 1.5 V. Therefore, applications using IGLOO or ProASIC3L devices powered by a 1.2 V supply must switch the core supply to 1.5 V for in-system programming.

The purpose of this document is to describe an easy-to-use and cost-effective solution for switching the core supply voltage from 1.2 V to 1.5 V during in-system programming for IGLOO and ProASIC3L devices.

2. VCC rises to 1.5 V before programming begins.

Figure 14-3 • Programming Algorithm

The oscilloscope plot in Figure 14-3 shows a wider time interval for the programming algorithm and includes the TDI and TMS signals from the FlashPro3. These signals carry the programming information that is programmed into the device and should only start toggling after the V_{CC} core voltage reaches 1.5 V. Again, TRST from FlashPro3 and the V_{CC} core voltage of the IGLOO device are labeled. As shown in Figure 14-3, TDI and TMS are floating initially, and the core voltage is 1.2 V. When a programming command on the FlashPro3 is executed, TRST is driven HIGH and TDI is momentarily driven to ground. In response to the HIGH TRST signal, the circuit responds and pulls the core voltage to 1.5 V. After 100 ms, TRST is briefly driven LOW by the FlashPro software. This is expected behavior that ensures the device JTAG state machine is in Reset prior to programming. TRST remains HIGH for the duration of the programming. It can be seen in Figure 14-3 that the VCC core voltage signal remains at 1.5 V for approximately 50 ms before information starts passing through on TDI and TMS. This confirms that the voltage switching circuit drives the VCC core supply voltage to 1.5 V prior to programming.



Microprocessor Programming of Microsemi's Low Power Flash Devices



Figure 15-3 • MCU FPGA Programming Model

FlashROM

Microsemi low power flash devices have 1 kbit of user-accessible, nonvolatile, FlashROM on-chip. This nonvolatile FlashROM can be programmed along with the core or on its own using the standard IEEE 1532 JTAG programming interface.

The FlashROM is architected as eight pages of 128 bits. Each page can be individually programmed (erased and written). Additionally, on-chip AES security decryption can be used selectively to load data securely into the FlashROM (e.g., over public or private networks, such as the Internet). Refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 133.

16 – Boundary Scan in Low Power Flash Devices

Boundary Scan

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 16-2 on page 360).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

TAP Controller State Machine

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 16-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.



Figure 16-1 • TAP Controller State Machine

UJTAG Applications in Microsemi's Low Power Flash Devices

UJTAG Support in Flash-Based Devices

The flash-based FPGAs listed in Table 17-1 support the UJTAG feature and the functions described in this document.

Table 17-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.